

**In the Specification:**

Please replace the paragraph at page 6, lines 3-15, with the following:

A process chamber component 22 having a surface 20 is cleaned to remove process deposits 24 that are generated during processing of a substrate 104, as shown for example in Figure 1. Performing a cleaning process to remove the deposits 24 can reduce the formation of contaminant particles in the chamber 106 and improve substrate yields. The process deposits 24 can comprise metal-containing deposits, such as deposits comprising at least one of tantalum, tantalum nitride, titanium, titanium nitride, aluminum, copper, tungsten, and tungsten nitride. The chamber components 22 cleaned in the process comprise those that accumulate process deposits 24, such as for example, as shown in Figure 3, a portion of a gas delivery system 112 that provides process gas in the chamber 106, a substrate support 114 that supports the substrate 104 in the chamber 106, a gas energizer 116 that energizes the process gas, chamber enclosure walls 118 and shields 120, or a gas exhaust 122 that exhausts gas from the chamber 106.